ECH8657

ON Semiconductor®

N-Channel Power MOSFET 35V, 4.5A, 59mΩ, Dual ECH8

http://onsemi.com

Features

- 4V drive
- · Halogen free compliance
- · Protection diode in

Specifications

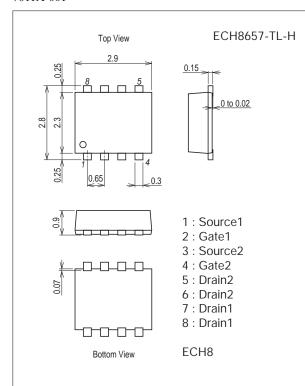
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		35	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		4.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	30	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm) 1unit	1.3	W
Total Dissipation	PT	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7011A-001



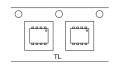
Product & Package Information

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

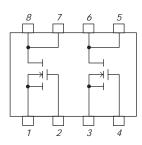
Packing Type: TL



Marking



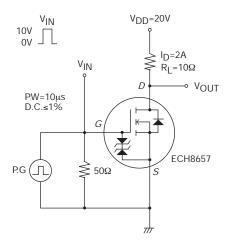
Electrical Connection



Electrical Characteristics at Ta=25°C

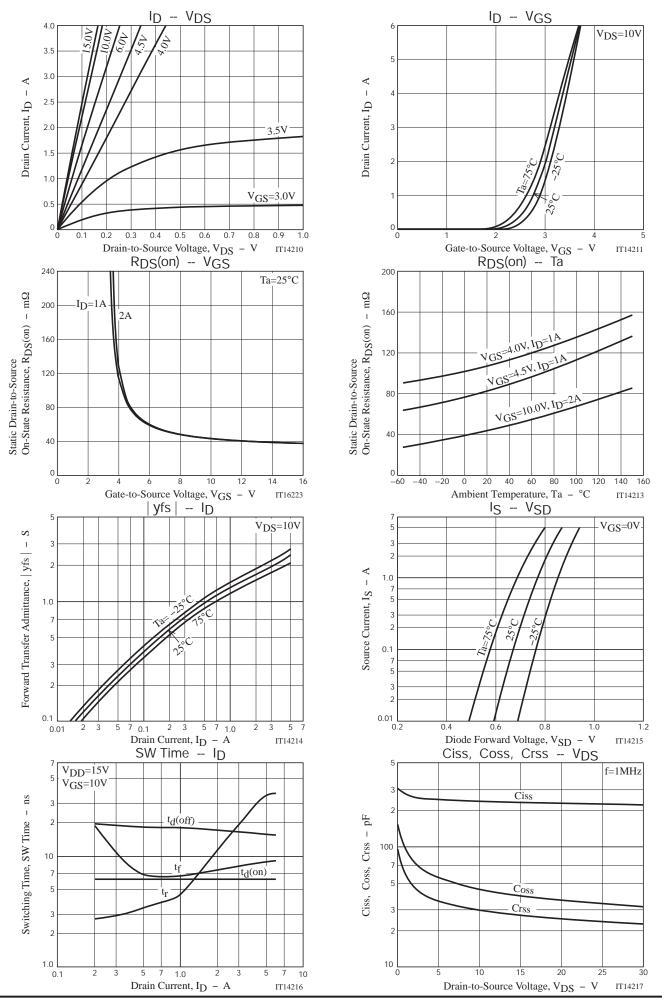
Parameter	Cumbal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions		typ	max	Uniii	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =35V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2A		1.66		S	
	R _{DS} (on)1	I _D =2A, V _G S=10V		45	59	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =1A, V _{GS} =4.5V		85	119	mΩ	
	R _{DS} (on)3	I _D =1A, V _{GS} =4V		110	155	mΩ	
Input Capacitance	Ciss			230		pF	
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		37		pF	
Reverse Transfer Capacitance	Crss			25		pF	
Turn-ON Delay Time	t _d (on)			6		ns	
Rise Time	t _r	Can appointed Toot Circuit		11		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		17		ns	
Fall Time	tf			9		ns	
Total Gate Charge	Qg			4.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =20V, V _{GS} =10V, I _D =4.5A		1.0		nC	
Gate-to-Drain "Miller" Charge	Qgd			1.0		nC	
Diode Forward Voltage	V _{SD}	I _S =4.5A, V _{GS} =0V		0.85	1.2	V	

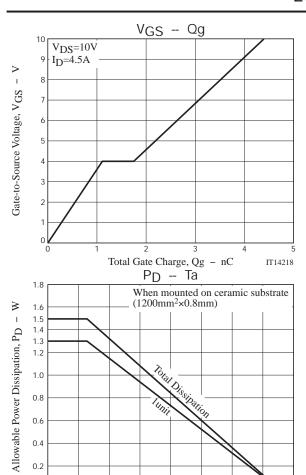
Switching Time Test Circuit



Ordering Information

Device	Device Package		memo	
ECH8657-TL-H	CH8657-TL-H ECH8		Pb Free and Halogen Free	





80

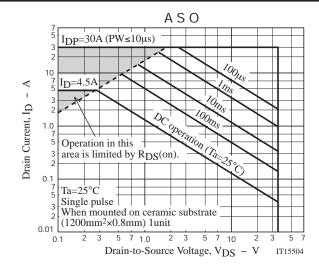
Ambient Temperature, Ta - °C

100

140

160

IT15505



0

0

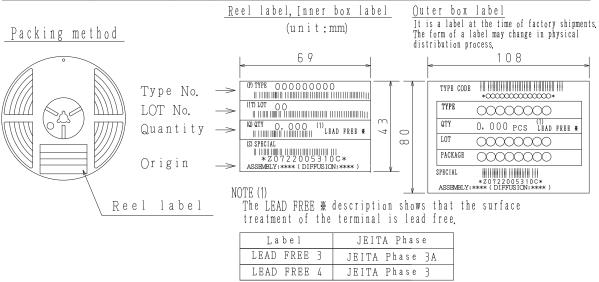
20

Embossed Taping Specification

ECH8657-TL-H

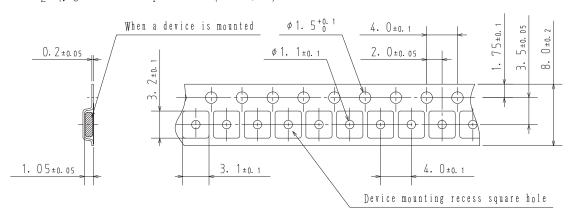
1. Packing Format

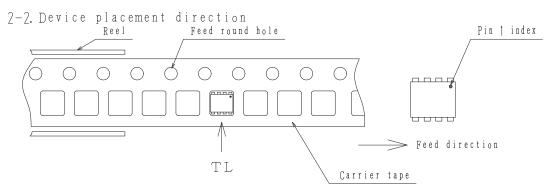
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)	
ЕСН8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



2. Taping configuration

2-1. Carrier tape size (unit:mm)





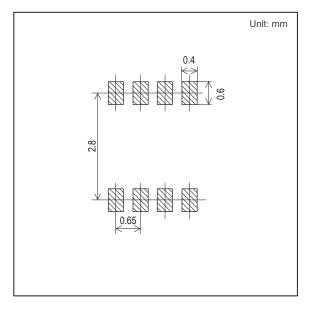
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8657-TL-H

Mass (g) Unit 0.02 * For reference mm 0. 15^{+0. 1}_{-0. 05} 0. 25±0.06 2. 9±0.06 0~0.02 2. 8±0. 05 2. 3±0.06 LOT No. 0. 25±0.06 0. 3^{+0. 1} PIN#1 0. 9±0. 05 0.05 \$ \$

Land Pattern Example



Note on usage: Since the ECH8657 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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